IN THE SPECIFICATION:

Please substitute the following paragraph for the abstract:

When a selection TFT ~~(20)~~ and a correction TFT ~~(22)~~ are turned on, a data voltage of a data line is stored in a storage capacitor ~~28~~ as a gate voltage of a driving TFT ~~(24)~~. After turning off the selection TFT ~~(20)~~, a voltage of a capacitor line SC falls, thereby turning on the driving TFT ~~(24)~~ to supply a driving current to an organic EL element ~~(26)~~. The correction TFT ~~(22)~~ is in the ON state before the capacitor line SC falls, and is turned off in the course of the fall of the line. Consequently, the capacitance of the correction TFT ~~(22)~~ changes during the fall of the gate voltage, and the gradient of the gate voltage fall of the driving TFT ~~(24)~~ is changed, thereby setting the gate voltage after the capacitor line SC falls in accordance with variation in threshold of the driving TFT ~~(24)~~. Particularly by disposing the driving TFT ~~(24)~~ and the correction TFT ~~(22)~~ adjacent to each other, the two TFTs are provided with the same properties to achieve effective correction.